

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
30V	6.4mΩ@10V	50A
	11mΩ@4.5V	

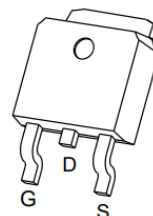
Feature

- Trench Technology Power MOSFET
- Low $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested

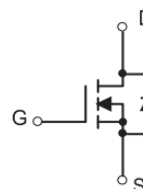
Application

- Power Management
- Load Switching

TO-252-2L



Schematic diagram



Package Marking and Ordering Information

Part Number	Package	Marking	Packing	Reel Size	Tape Width	Qty
GPM064N03LTF	TO-252-2L	M064N03L	Reel & Tape	330mm	16mm	2500pcs

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current ¹	$T_C = 25^{\circ}\text{C}$	I_D	50	A
	$T_C = 100^{\circ}\text{C}$		32	
Pulsed Drain Current ²		I_{DM}	200	A
Single Pulsed Avalanche Current ³		I_{AS}	18	A
Single Pulsed Avalanche Energy ³		E_{AS}	81	mJ
Power Dissipation ⁵		P_D	45	W
$T_C = 25^{\circ}\text{C}$				
Thermal Resistance from Junction to Ambient ⁶		$R_{\theta JA}$	50	$^{\circ}\text{C/W}$
Thermal Resistance from Junction to Case		$R_{\theta JC}$	2.8	$^{\circ}\text{C/W}$
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~ +150	$^{\circ}\text{C}$

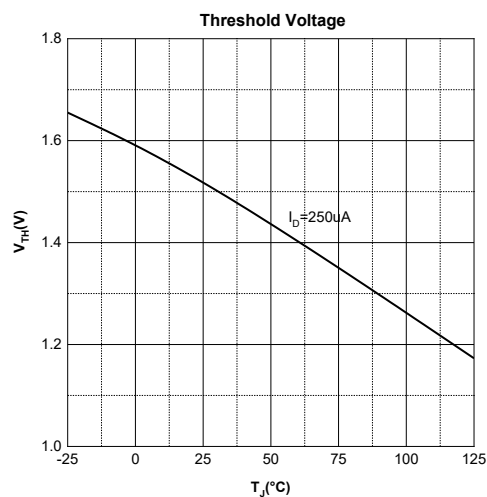
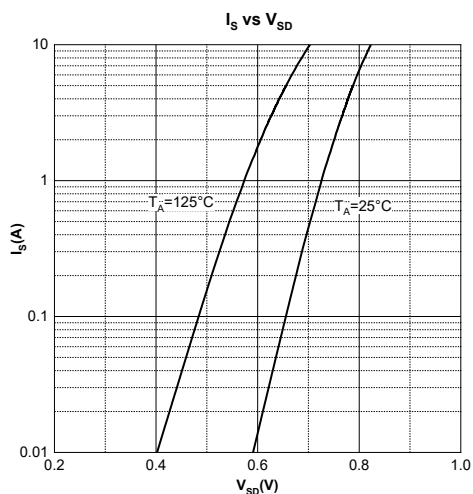
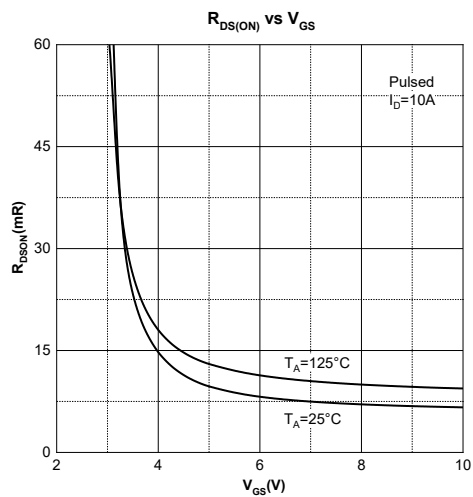
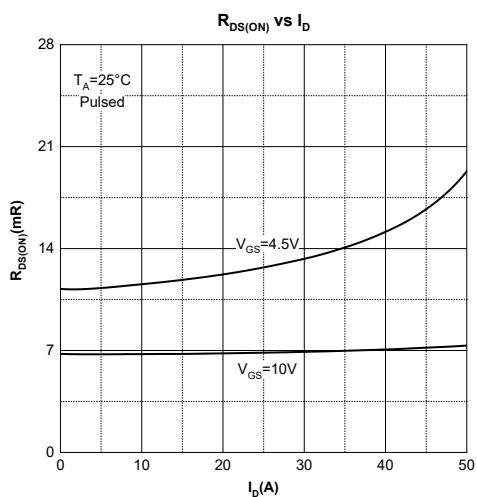
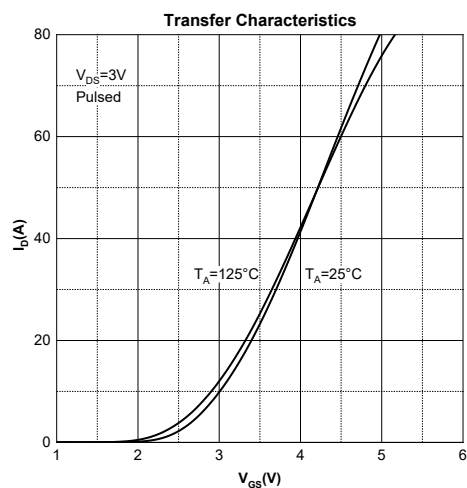
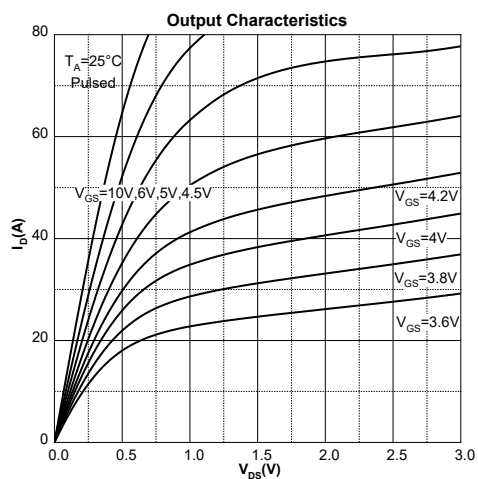
MOSFET ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

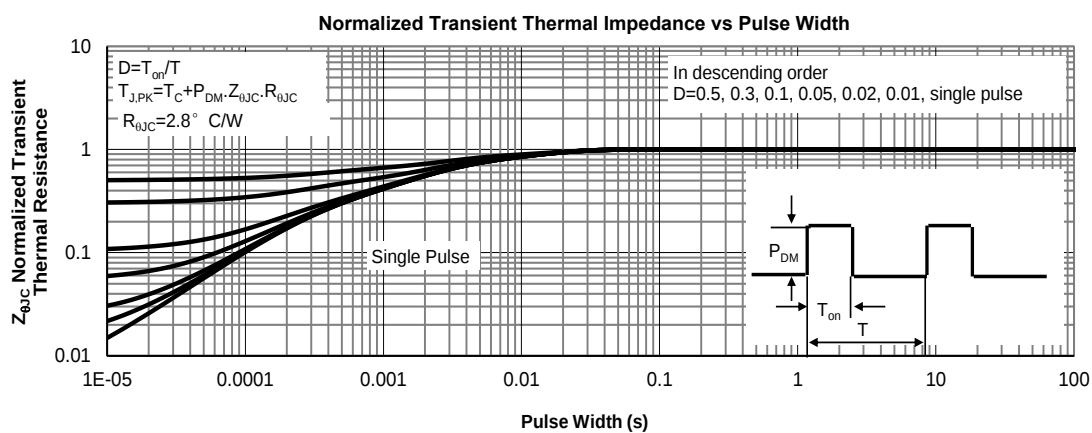
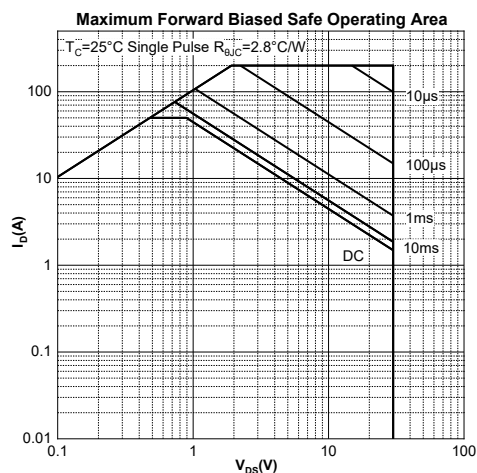
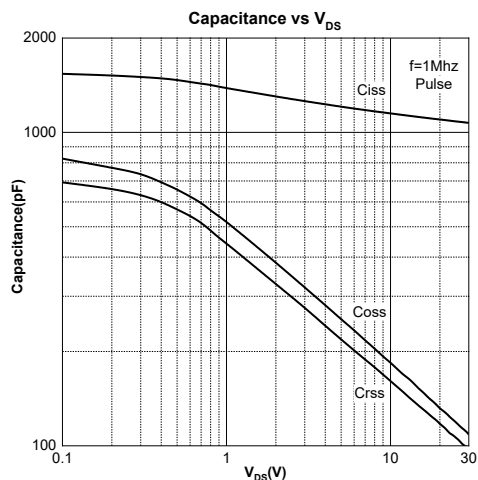
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30V, V _{GS} = 0V			1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±100	nA
On Characteristics ⁴						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1	1.5	2	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 10A		6.4	8.6	mΩ
		V _{GS} = 4.5V, I _D = 10A		11	15	
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} = 15V, V _{GS} = 0V, f = 1MHz		1100		pF
Output Capacitance	C _{oss}			153		
Reverse Transfer Capacitance	C _{rss}			134		
Gate Resistance	R _g	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz		2.2		Ω
Switching Characteristics						
Total Gate Charge	Q _g	V _{DS} = 15V, V _{GS} = 10V, I _D = 10A		24		nC
Gate-Source Charge	Q _{gs}			3.3		
Gate-Drain Charge	Q _{gd}			6		
Turn-On Delay Time	t _{d(on)}	V _{DD} = 15V, V _{GS} = 10V, R _G = 3Ω, R _L = 0.75Ω		10		ns
Turn-On Rise Time	t _r			14		
Turn-Off Delay Time	t _{d(off)}			33		
Turn-Off Fall Time	t _f			8		
Source-Drain Diode Characteristics						
Diode Forward Voltage ⁴	V _{SD}	V _{GS} = 0V, I _S = 10A			1.2	V

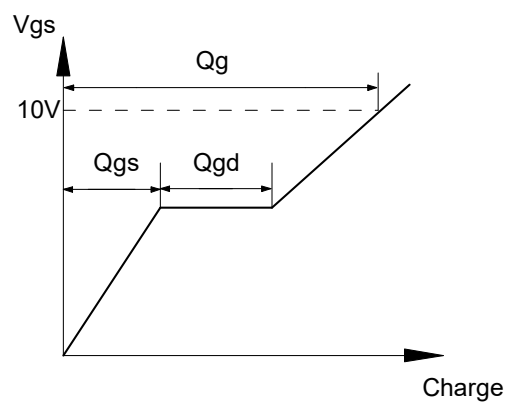
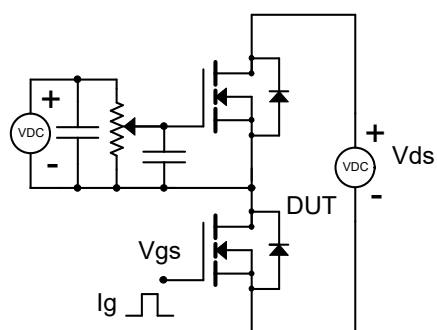
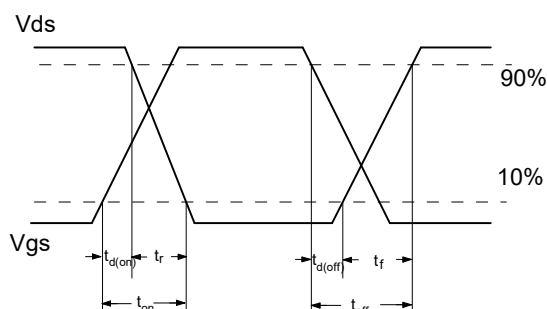
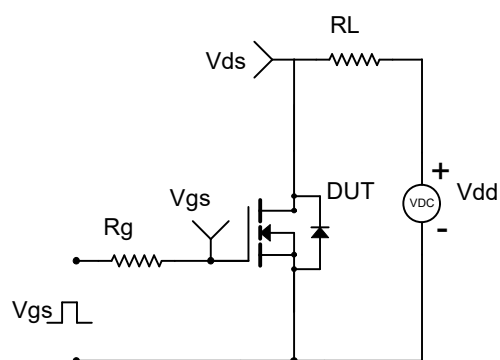
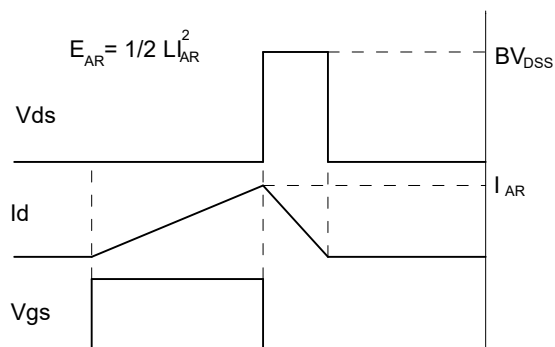
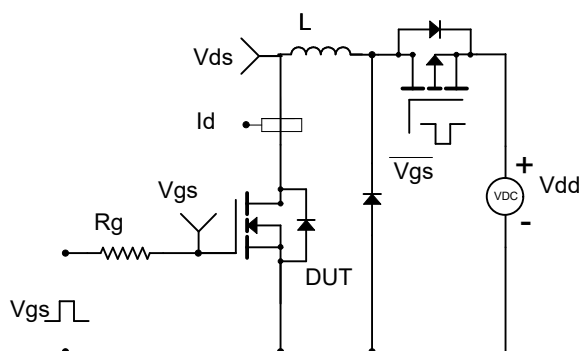
Notes:

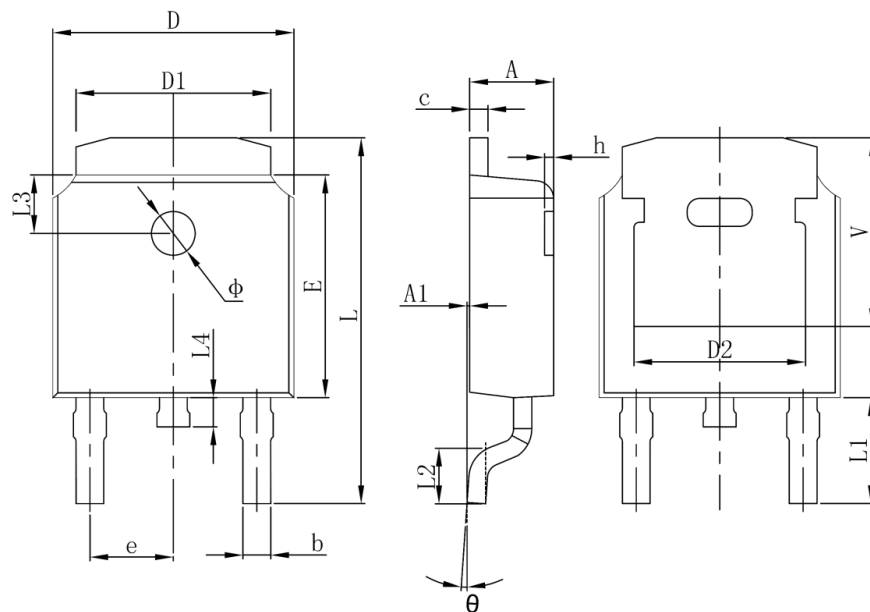
- 1.The maximum current rating is limited by package. And device mounted on a large heatsink.
- 2.Pulse Test: Pulse Width ≤ 10μs, duty cycle ≤ 1%.
- 3.EAS condition: V_{DD} = 30V, V_{GS} = 10V, L = 0.5mH, R_G = 25Ω Starting T_J = 25°C.
- 4.Pulse Test: Pulse Width ≤ 300μs, duty cycle ≤ 2%.
- 5.The power dissipation P_D is limited by T_{J(MAX)} = 150°C. And device mounted on a large heatsink.
- 6.Device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A = 25°C.

Typical Characteristics





Test Circuit
Gate Charge Test Circuit & Waveform

Resistive Switching Test Circuit & Waveform

Unclamped Inductive Switching (UIS) Test Circuit & Waveforms


TO-252-2L Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.860	0.025	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830REF		0.190REF	
E	6.000	6.300	0.236	0.248
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.382	0.406
L1	2.900REF		0.114REF	
L2	1.400	1.700	0.055	0.067
L3	1.600REF		0.063REF	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250REF		0.207REF	

Attention:

- GreenPower Electronics reserves the right to improve product design function and reliability without notice.
- Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.
- GreenPower Electronics products belong to consumer electronics or other civilian electronic products.